JMSL0302PU

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% Vds Tested
- Halogen-free; RoHS-compliant
- Pb-free plating

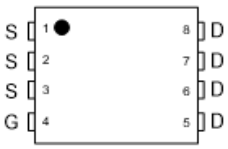
Applications

- Load Switch
- PWM Application
- Power Management

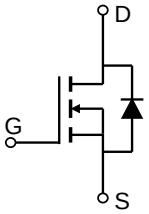
Product Summary

Parameters	Value	Unit
V_{DSS}	30	V
$V_{GS(th)_Typ}$	1.5	V
I_D(@V_{GS}=10V)	125	A
$R_{DS(ON)_Typ}$(@V_{GS}=10V)	1.4	mΩ
$R_{DS(ON)_Typ}$(@V_{GS}=4.5V)	2.0	mΩ

PDFN3x3-8L



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSL0302PU-13	SL0302P	1	Tape&Reel	PDFN3x3-8L	5000	50000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		30	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	125	A
		T_C = 100°C	79	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		294	mJ
P_D	Power Dissipation	T_C = 25°C	50	W
		T_C = 100°C	20	
T_J $_{STG}$	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
R	Thermal Resistance, Junction to Ambient(3)	43	°C/W
R	Thermal Resistance, Junction to Case	2.5	

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24V, V_{GS} = 0V	-	-	1.0	μ
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.1	1.5	2.2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 20A	-	1.4	2.0	mΩ
		V_{GS} = 4.5, I_D = 15A	-	2.0	2.6	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	1.7	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz	-	2936	4403	pF
C_{oss}	Output Capacitance		-	1716	2573	pF
C_{rss}	Reverse Transfer Capacitance		-	50	100	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 15V, I_D = 20A	-	47	-	nC
Q_{gs}	Gate Source Charge		-	8.5	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	8.6	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 15V I_D= 20A, R_{GEN} = 3Ω	-	10	-	ns
t_r	Turn-On Rise Time		-	29	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	39	-	ns
t_f	Turn-Off Fall Time		-	11	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	125	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	500	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	-	49	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	49	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25C, V_{DD}=30V, V_{GS}=10V, R_G=25ohm, L=3mH, I_{AS}=14A, V_{DD}=0V during time in avalanche.

3. R is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.

4. Pulse Test: Pulse Width ≤ ≤ 0.5%.

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Typical Performance Characteristics

Figure 1: Power De-rating

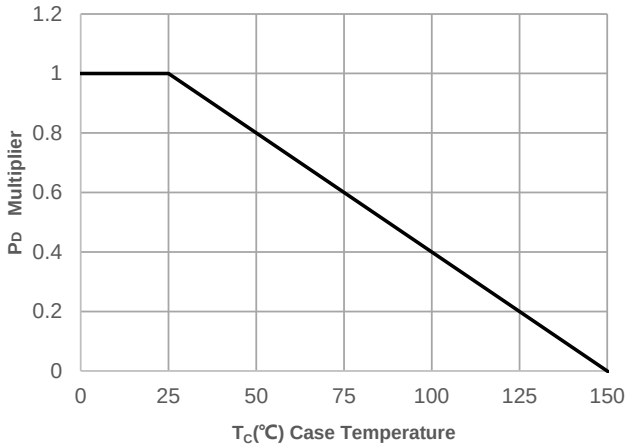


Figure 2: Current De-rating

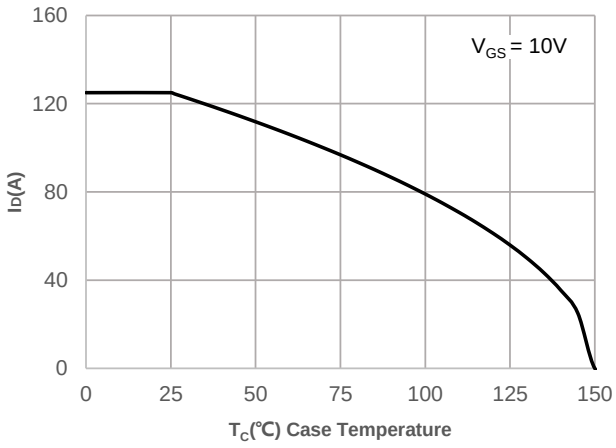
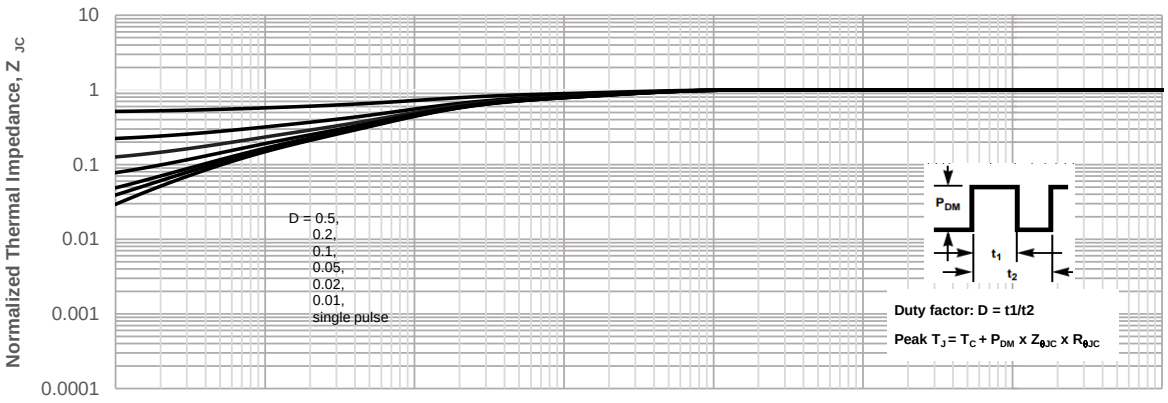
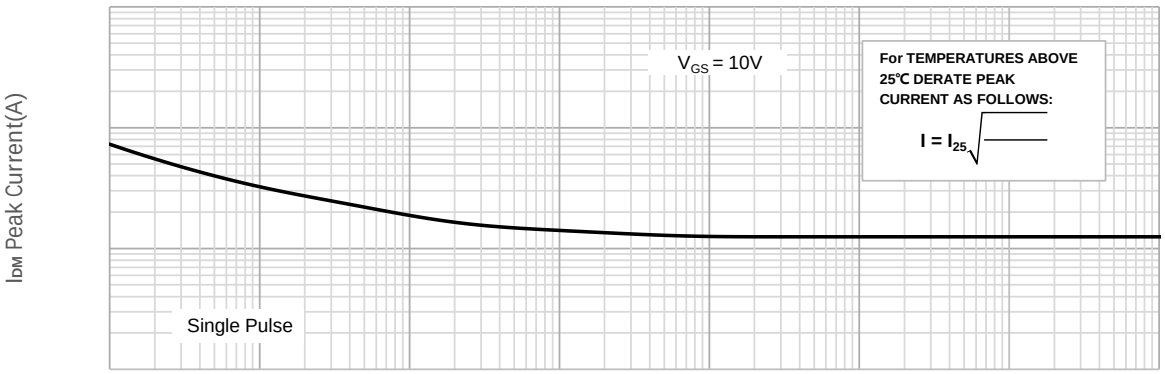


Figure 3: Normalized Maximum Transient Thermal Impedance



t, Rectangular Pulse Width (s)

Figure 4: Peak Current Capacity



t, Rectangular Pulse Width (s)

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Typical Performance Characteristics

Figure 5: Output Characteristics

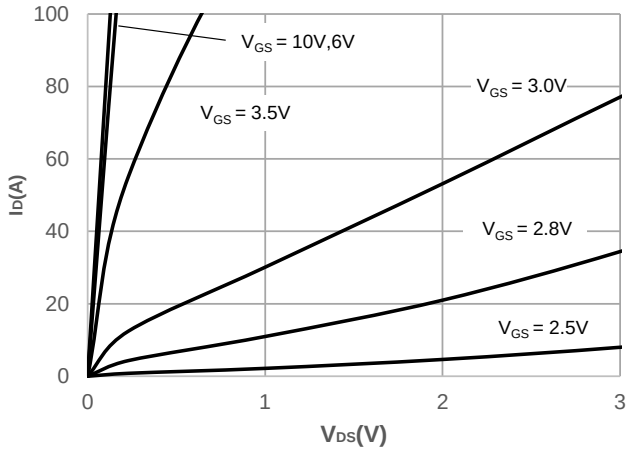


Figure 6: Typical Transfer Characteristics

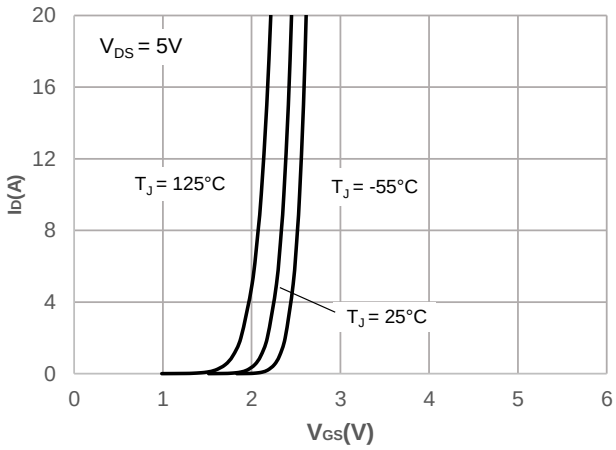


Figure 7: On-resistance vs. Drain Current

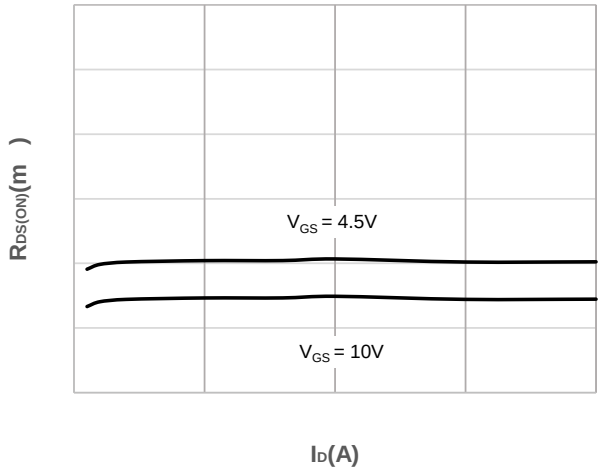


Figure 8: Body Diode Characteristics

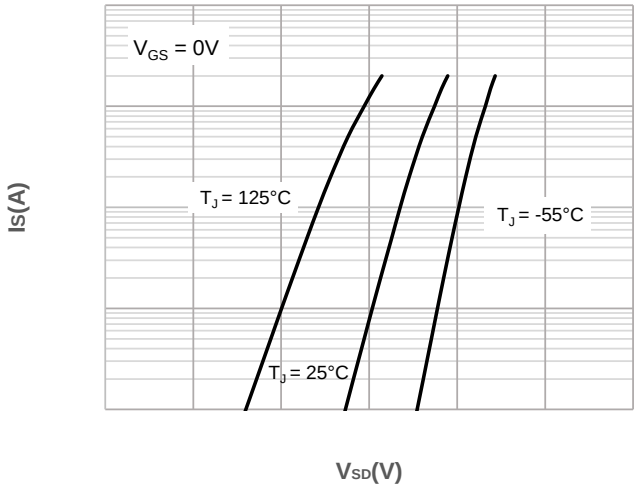


Figure 9: Gate Charge Characteristics

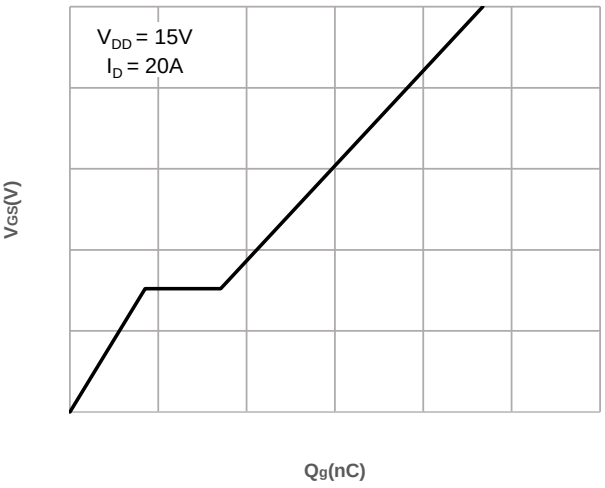
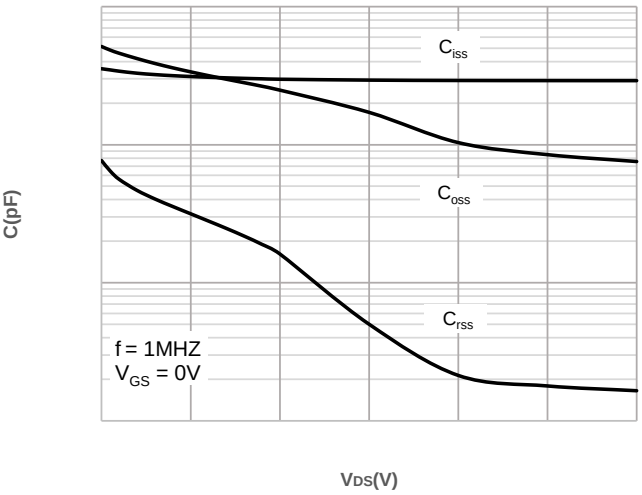


Figure 10: Capacitance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

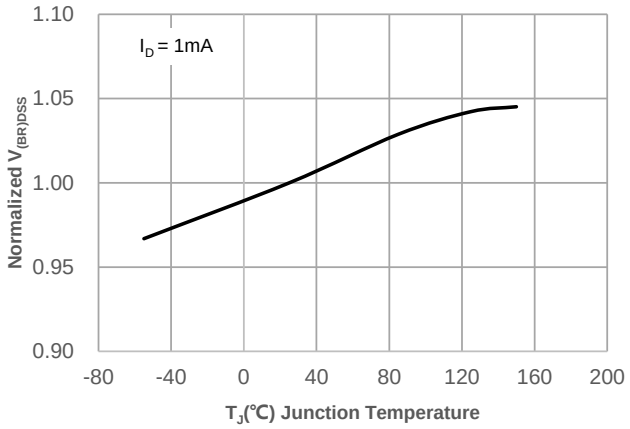


Figure 12: Normalized on Resistance vs. Junction Temperature

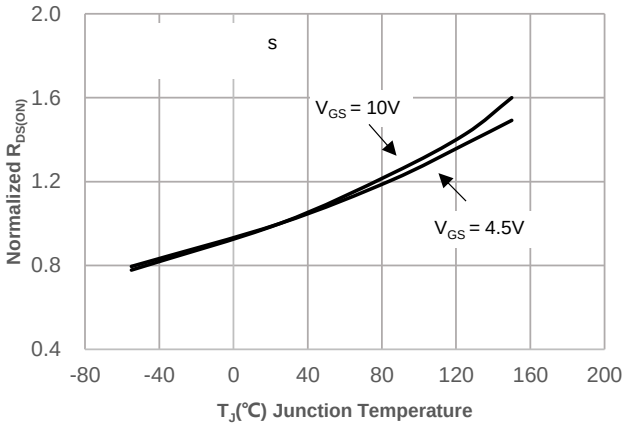


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

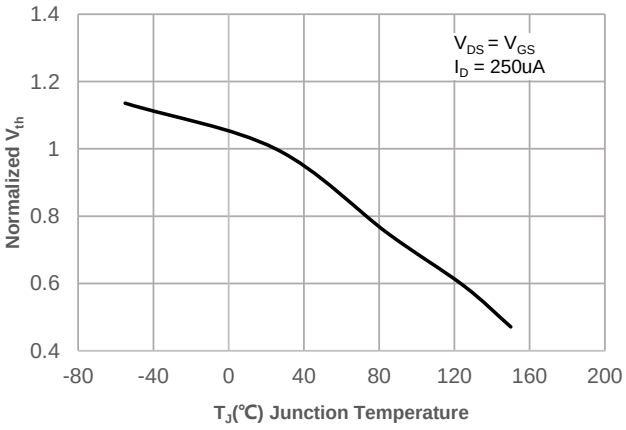


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

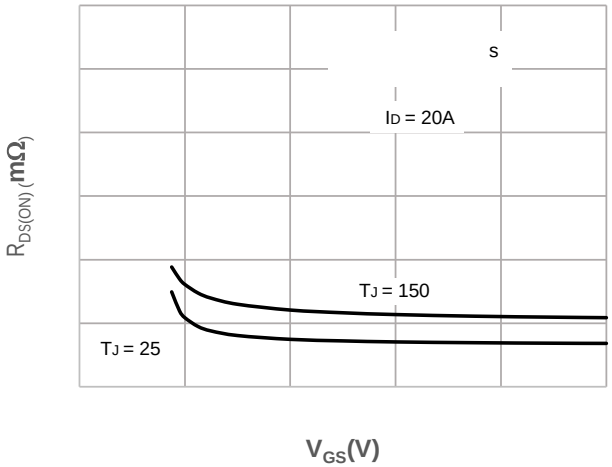
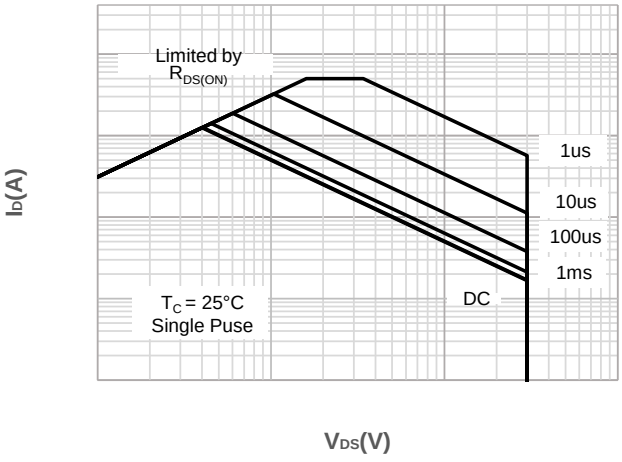


Figure 15: Maximum Safe Operating Area



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Test Circuit

Figure 1: Gate Charge Test Circuit & Waveform

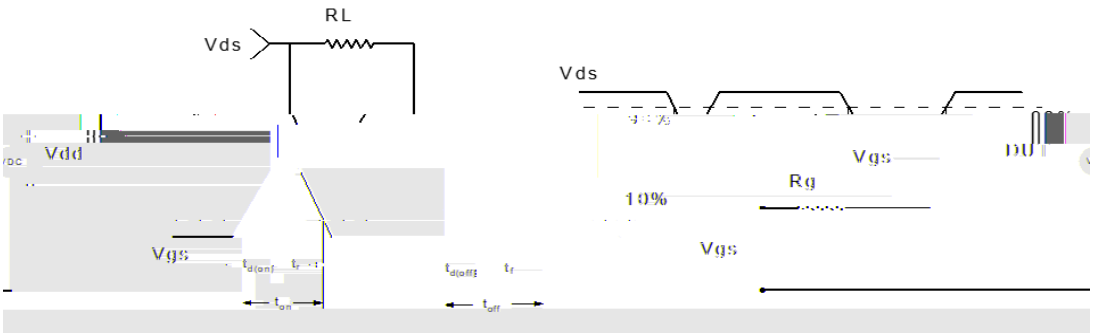

Figure 2: Resistive Switching Test Circuit & Waveform

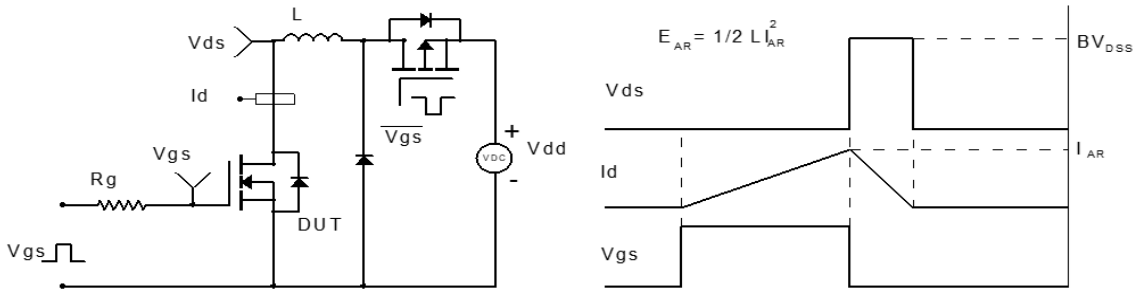

Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

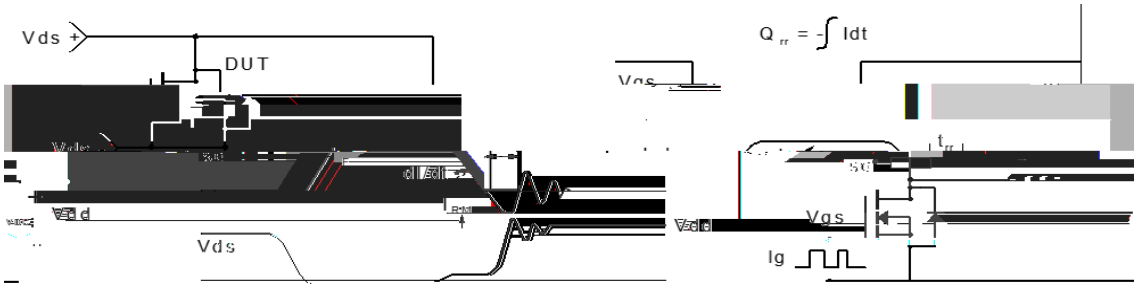

Figure 4: Diode Recovery Test Circuit & Waveform

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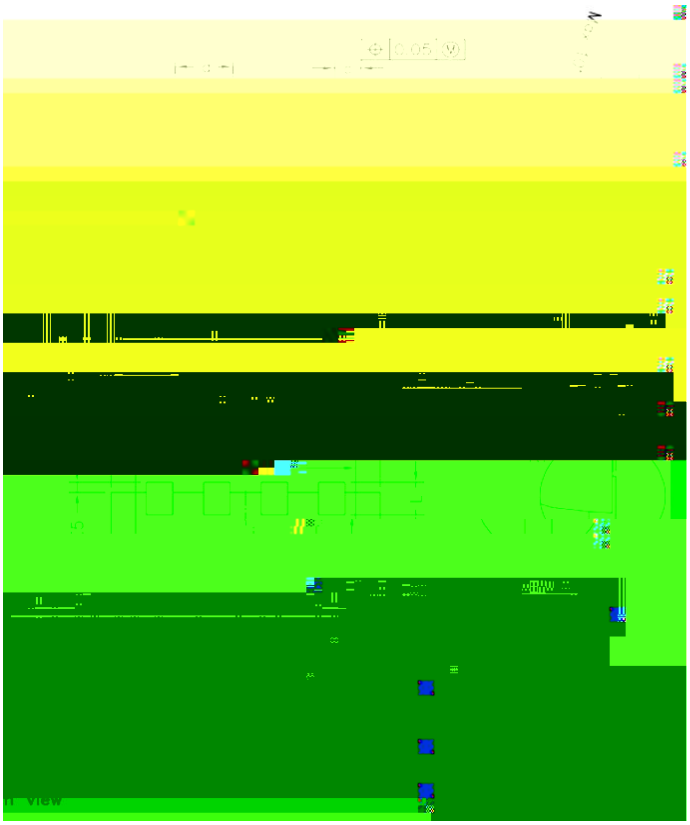
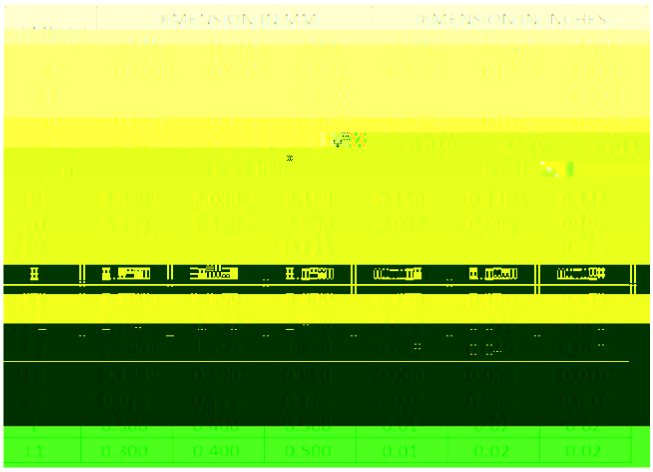
Package Mechanical Data(PDFN3x3-8L)

Package Outline





DIMENSION IN MM			DIMENSION IN INCHES		
L1	0.300	0.400	0.500	0.01	0.02	0.02

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